

# **isc** Silicon PNP Power Transistor

### **DESCRIPTION**

- · High DC Current Gain
- Complement to type BD337
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

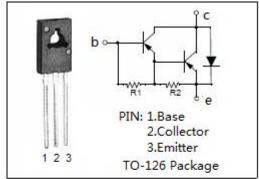
 PNP epitaxial base transistors in monolithic Darlington circuit for audio output stages and general amplifier and switching applications.

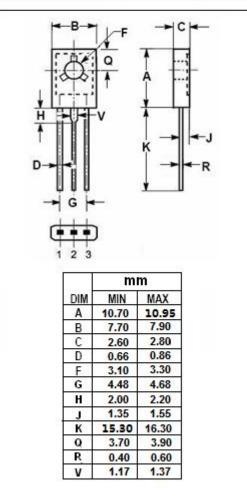
# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{\text{CEO}}$	Collector-Emitter Voltage	-120	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
Ic	Collector Current-Continuous	-6	Α
I <sub>BM</sub>	Base Current-Peak	-0.15	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C  60		W
TJ	Junction Temperature 150		$^{\circ}\!\mathbb{C}$
T <sub>stg</sub>	Storage Temperature Range -65~150		$^{\circ}\!\mathbb{C}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance,Junction to Case	2.08	°C/W
R <sub>th j-a</sub>	R <sub>th j-a</sub> Thermal Resistance, Junction to Ambient		°C/W







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**BD338** 

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = 0	-120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =- 3A; I <sub>B</sub> = -12mA			-2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -3A; V <sub>CE</sub> = -3V			-2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -120V; I <sub>E</sub> = 0 V <sub>CB</sub> = -120V; I <sub>E</sub> = 0,T <sub>C</sub> =150°C			-0.1 -1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-5	mA
h <sub>FE-1</sub> *	DC Current Gain	Ic= -0.5A; Vc== -3V		2700		
h <sub>FE-2</sub> *	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> =-3V	750			
h <sub>FE-3</sub> *	DC Current Gain	I <sub>C</sub> = -6A; V <sub>CE</sub> = -3V		400		

<sup>\*:</sup>Measured under pulse conditions:tp<300us, \u00f3<2%

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